

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	3.5	kV

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX. 10	mA
V_{GT}		- -	MAX. 1	V

$V_{GD} \leq 12V$ (unless otherwise specified)

ORDERING INFORMATION

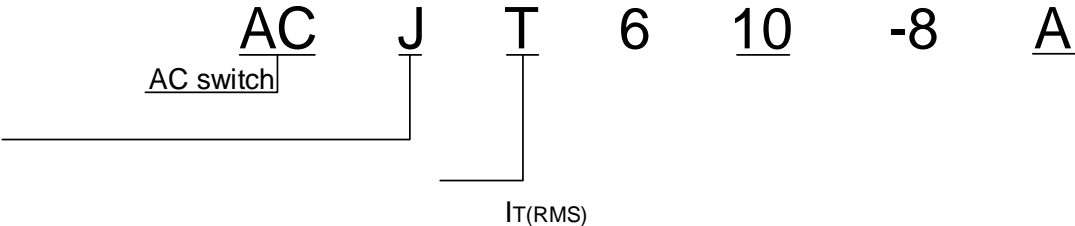


FIG.1: Maximum power dissipation versus RMS on-state current

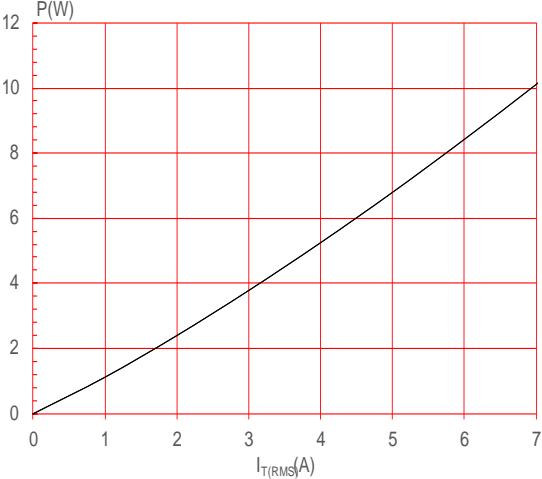
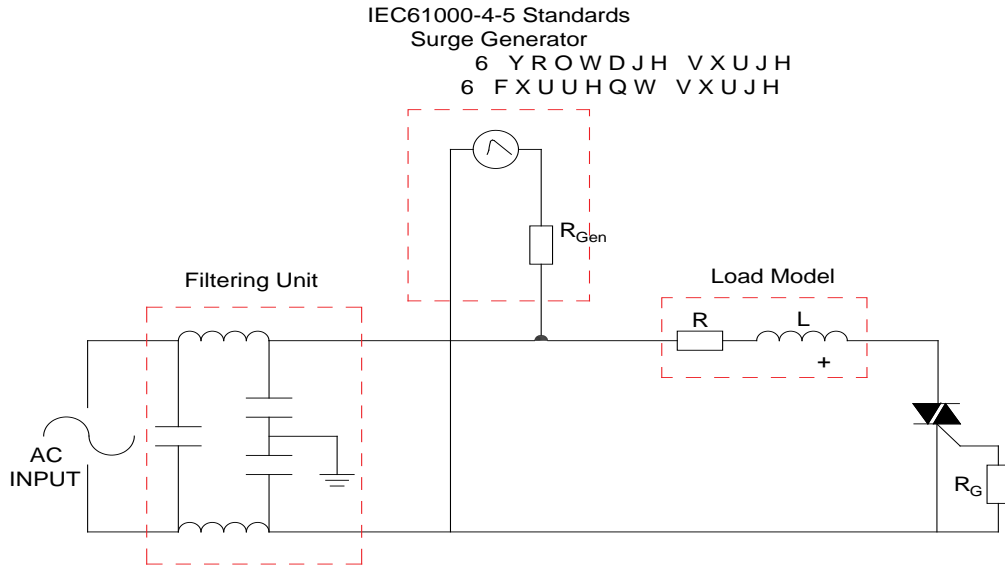


FIG.2: RMS on-state current versus case temperature


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



PAC103 0 T DGJ /T (JTJ7 (c) M)-5-125E1E64t1H1A64tjwCA64t

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